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Examiner Initials*	Gite No.'	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s) publisher city and/or country where published	T²
Sw		S. ISHIBASDHI, Y. HIGUCHI, Y. OTA & K. NAKAMURA, "Low Resistivity Indium-Tin Oxide Transparent Conductive Films. II. Effect of Sputtering Voltage on Electrical Property of Films", American Vacuum Society, May/June 1990, pp. 1403-1406, Volume 8, No. 3, Japan.	
Spr		YUZO SHIGESATO, SATORU TAKAKI & TAKESHI HARANOH, "Electrical and Structural Properties of Low Resistivity Tin-Doped Indium Oxide Films", American Institute of Physics, April 1992, pp. 3356-3363, Japan.	
Ser.		EIJI MINAMI ET AL., Extended Abstracts (The 46 th Spring Meeting, 1999).	
An		Y. SHIGESATO, "Technology for Transparent Conductive Film", p. 112, Ohmsha.	
XV		PREM NATH, R.F. BUNSHAH, B.M. BASON AND O.M. STAFFSUD, "Electrical and Opitical Properties of In₂O₃: Sn Films Prepared by Activated Reactive Evaporation", <i>Thin Solid Films</i> , 72 (1980), pp. 463-468.	
XV	7	SWATI RAY, RATNABALI BANERJEE, N. BASU, A.K. BATABYAL, AND A.K. BARUA, "Properties of Tin Doped Indium Oxide Thin Films Prepared by Magnetron Sputtering", American Institute of Physics, 1983, pp. 3497-3501.	
X		I.A. RAUF, "A Novel Method for Preparing Thin Films with Selective Doping in a Single Evaporation Step," Journal of Materials Science Letters 12 (1993), pp. 1902-1905/	
Ju	-\	I.A. RAUF, "Structure and Properties of Tin-Doped Indium Oxide Thin Films Prepared by Reactive Electron-Beam Evaporation with a Zone-Confining Arrangement," American Institute of Physics, 1996, pp. 4057-4065.	
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